

# RT3J11M

Composite Transistor  
For high speed switching  
Silicon P-channel MOSFET

## DESCRIPTION

RT3J11M is a composite transistor built with two INJ0001AX chips in SC-88 package.

## FEATURE

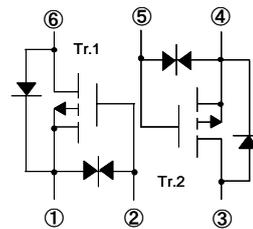
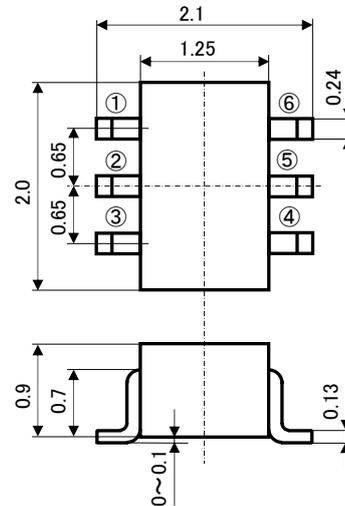
- Input impedance is high, and not necessary to consider a drive electric current.
- Drive voltage  $-2.5V$
- Low on Resistance.  $R_{ON}=7\Omega$  (TYP)
- High speed switching.
- Small package for easy mounting.

## APPLICATION

High speed switching , Analog switching

## OUTLINE DRAWING

Unit: mm



### TERMINAL CONNECTOR

- ①: SOURCE1
- ②: GATE1
- ③: DRAIN2
- ④: SOURCE2
- ⑤: GATE2
- ⑥: DRAIN1

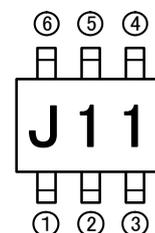
JEITA: SC-88

## MAXIMUM RATING ( $T_a=25^\circ C$ ) (Tr1, Tr2 Common)

SYMBOL	PARAMETER	RATING	UNIT
$V_{DSS}$	Drain-source voltage	-50	V
$V_{GSS}$	Gate-source voltage	$\pm 8$	V
$I_D$	Drain current(DC)	-100	mA
$I_{DP}$	Drain current(Pulse)	-400(※1)	mA
$P_D$	Total power dissipation	150	mW
$T_{ch}$	Channel temperature	+150	$^\circ C$
$T_{stg}$	Range of Storage temperature	-55 ~ +150	$^\circ C$

※1:  $P_w \leq 10\mu s$ , Duty cycle  $\leq 1\%$

## MARKING



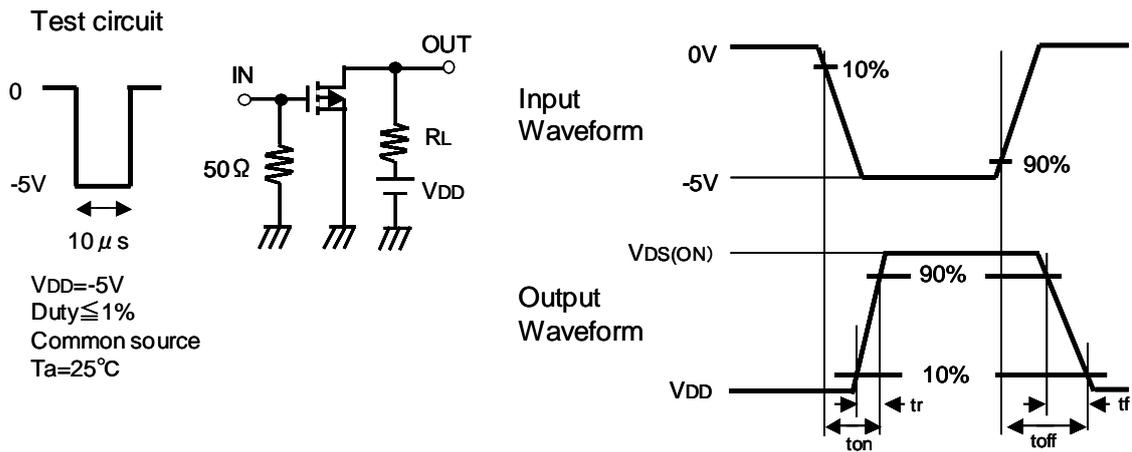
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## ELECTRICAL CHARACTERISTICS (Ta=25°C) (Tr1,Tr2 Common)

SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
			MIN	TYP	MAX	
V(BR)DSS	Drain-source breakdown voltage	Id=-100μA, Vgs=0V	-50	-	-	V
IGSS	Gate-source leak current	Vgs=±5V, Vds=0V	-	-	±0.5	μA
IDSS	Zero gate voltage drain current	Vds=-50V, Vgs=0V	-	-	-1.0	μA
Vth	Gate threshold voltage	Id=-250μA, Vds=Vgs	-0.6	-	-1.2	V
Yfs	Forward transfer admittance	Vds=-10V, Id=-0.1A	-	220	-	mS
RDS(ON)	Static drain-source on-state resistance	Id=-100mA, Vgs=-4.0V	-	7.0	-	Ω
Ciss	Input capacitance	Vds=-10V, Vgs=0V, f=1MHz	-	28	-	pF
Coss	Output capacitance		-	5.2	-	
ton	Switching time	VDD=-5V, Id=-10mA	-	13	-	ns
toff		Vgs=0~-5V	-	135	-	

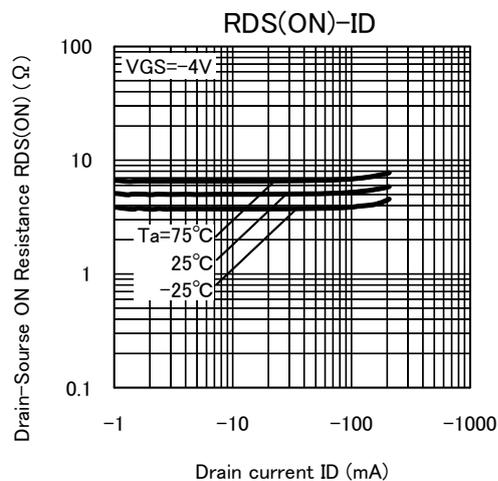
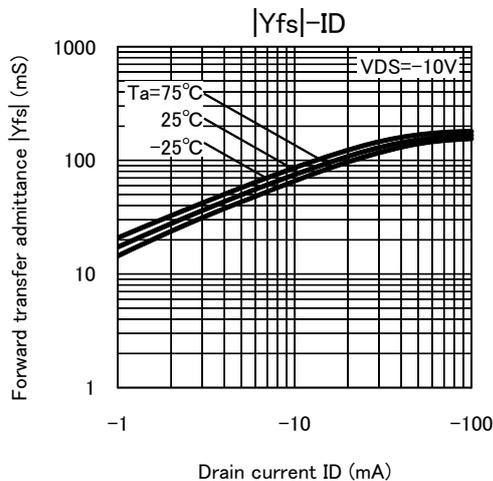
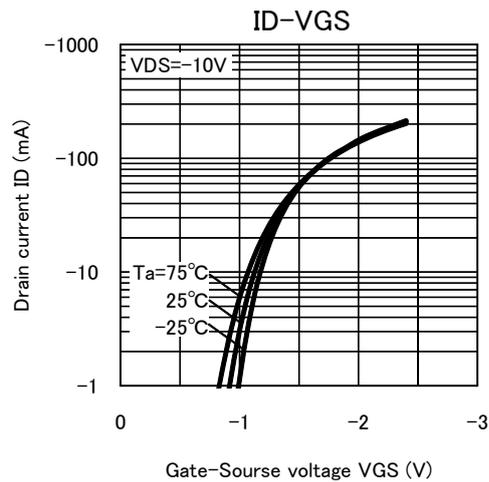
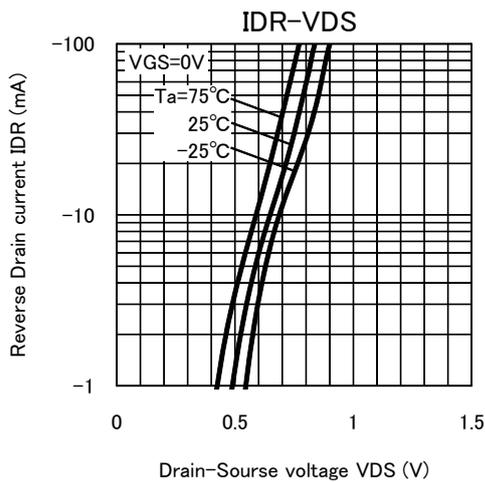
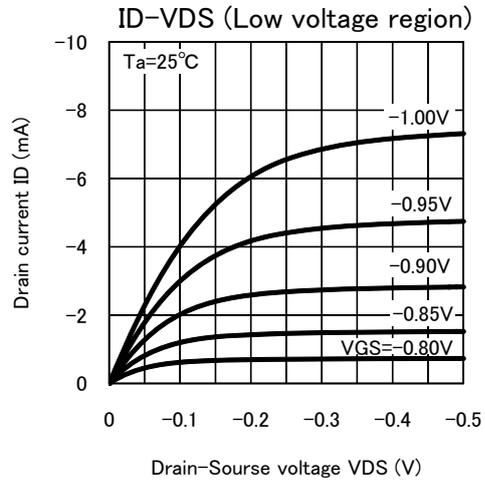
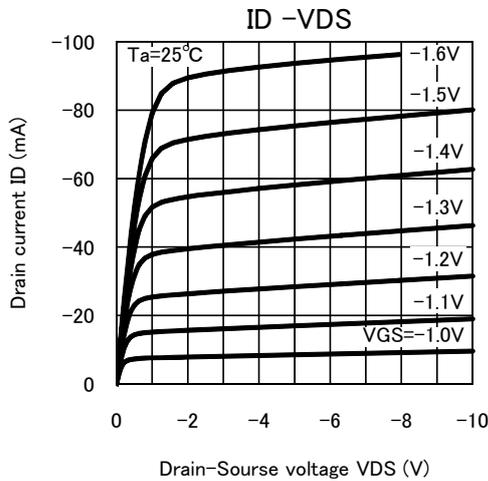
### Switching time test condition



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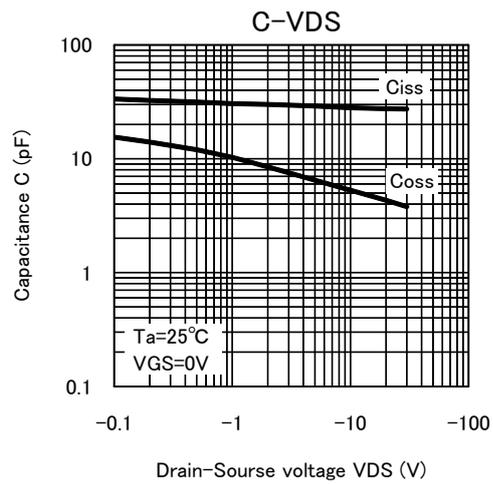
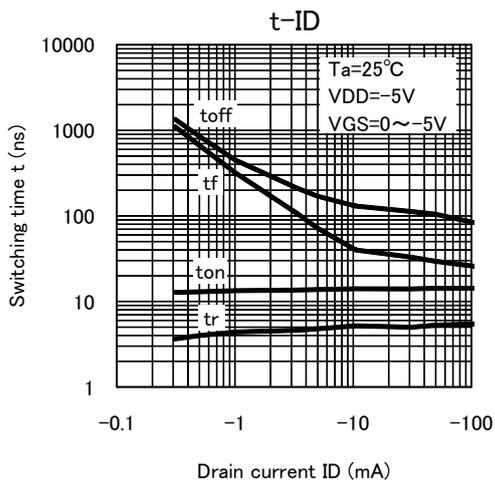
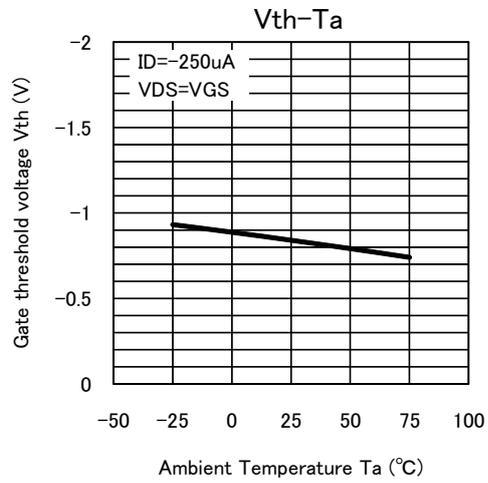
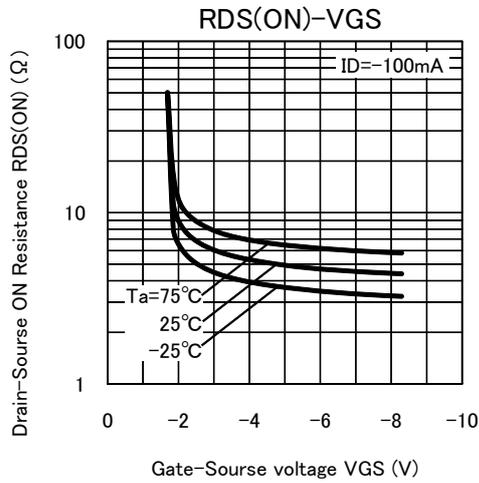
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## TYPICAL CHARACTERISTICS (Tr1,Tr2 Common)



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**Keep safety first in your circuit designs!**

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